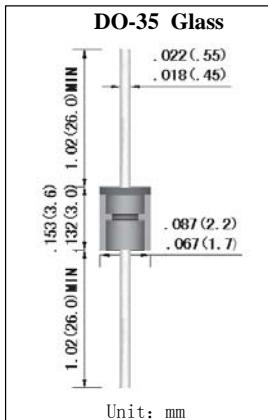


双向触发二极管

SILICON BIDIRECTIONAL DIAC



特征 Features

- 反向漏电流低 Low reverse leakage
- 正向浪涌承受能力较强 High forward surge capability
- 高温焊接保证 High temperature soldering guaranteed:
260°C/10 秒, 0.375" (9.5mm)引线长度。
- 260°C/10 seconds, 0.375" (9.5mm) lead length,
- 引线可承受5 磅 (2.3kg) 拉力。5 lbs. (2.3kg) tension
- 引线和管体皆符合RoHS标准。
Lead and body according with RoHS standard

机械数据 Mechanical Data

- 端子: 镀锡轴向引线 Terminals: Plated axial leads
- 安装位置: 任意 Mounting Position: Any

极限参数(LIMITING VALUES)

符号 Symbols	参数 Parameters	Value		单位 Unit
		DB3/DB4		
P _c	功耗 Power Dissipation	T _A =50°C	150	mW
I _{TRM}	峰值脉冲电压 Repetitive Peak on-state Current	t _p =10μS F=100Hz	2.0	A
T _{STG}	贮存 温度范围 Storage Temperature		-40 to +125	°C
T _J	工作结温范围 Operating Junction Temperature		-40 to +100	°C

电特性(ELECTRICAL CHARACTERISTICS)

符号 Symbols	参数 Parameters	测试条件 Test Conditions	Value		单位 Unit
			DB3	DB4	
V _{BO}	击穿电压 Breakover Voltage [Note 2]	C=22nF [Note 2] See Diagram 1	Min	28	V
			Typ	32	
			Max	36	
+V _{BO} - V _{BO}	击穿电压对称性 Breakover Voltage Symmetry	C=22nF [Note 2] See Diagram 1	Max	± 3	V
I ± ΔVI	动态回弹电压 Dynamic Breakover Voltage [Note 1]	ΔI=[I _{BO} to IF=10mA] See Diagram 1	Min	5	V
V _o	输出电压 Output Voltage [Note 1]	See Diagram 2	Min	5	V
I _{BO}	击穿电流 Breakover Current [Note 1]	C=22nF [Note 2]	Max	100	uA
tr	上升时间 Rise Time [Note 1]	See Diagram 3	Typ	1.5	uS
I _B	漏电流 Leakage Current [Note 1]	V _{BBO} =0.5V max See Diagram 1	Max	10	uA
I _P	峰值电流 Peak Current [Note 1]	See Diagram 2 (Gate)	Min	0.3	A

Notes:1.Electrical characteristics applicable in both forward and reverse directions.

2.Connected in parallel with the devices.

DIAGRAM 1: Current-voltage characteristics

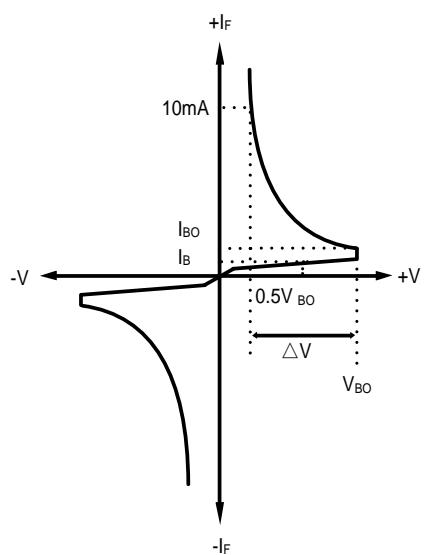


DIAGRAM 2: Test circuit for output voltage

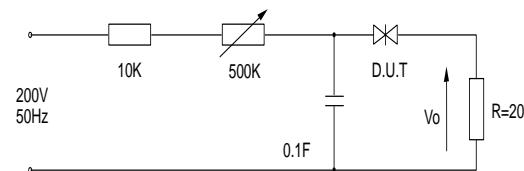


DIAGRAM 3: Test circuit see diagram 2

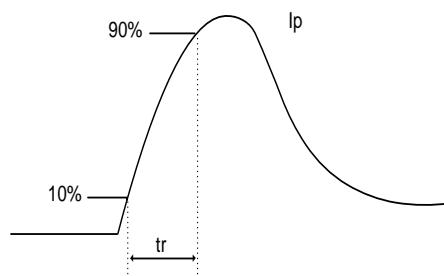


FIG.1-Power dissipation versus ambient temperature (maximum values)

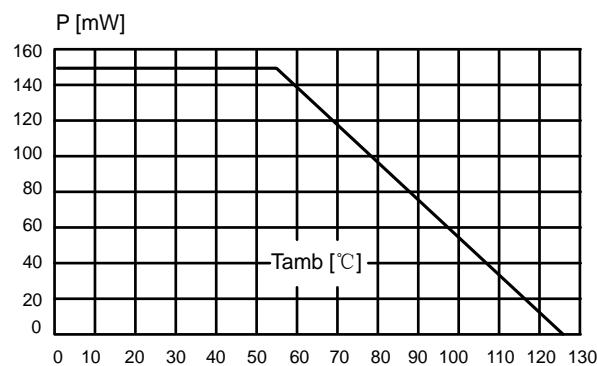


FIG.2-Peck pulse current versus pluse duration (maximum values)

